

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:) Confirmation No.: 1310
Koichiro TANAKA et al.) Examiner: Bradley Smith
Patent No. 7,737,053) Group Art Unit: 2894
Serial No. 10/579,239)
Filed: May 12, 2006)
For: SEMICONDUCTOR DEVICE AND)
MANUFACTURING METHOD OF)
THE SAME)

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR § 1.322 FOR
CORRECTION OF OFFICE MISTAKE

ATTN: Certificate of Correction Branch
Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

As provided in detail in the attached, the patentee respectfully requests that a Certificate of Correction be granted in the above-identified patent to correct mistakes in a patent, incurred through the fault of the Office.

Under 37 CFR 1.322, "The Commissioner may issue a certificate of correction pursuant to 35 U.S.C. 254 to correct a mistake in a patent, incurred through the fault of the Office, which mistake is clearly disclosed in the records of the Office at the request of the patentee or the patentee's assignee."

The patentee furthermore requests Expedited Issuance of this Certificate of Correction in accordance with MPEP § 1480.01. Specifically, this section provides that:

In an effort to reduce the overall time required in processing and granting Certificate of Correction requests, the Office will expedite processing and granting of patentee requests where such requests are

accompanied by evidence to show that the error is attributable solely to the Office Where the correction requested was incurred through the fault of the Office, and the matter is clearly disclosed in the records of the Office, and is accompanied by documentation that unequivocally supports the patentee's assertion(s), a Certificate of Correction will be expeditiously issued. MPEP § 1480.01

The following errors appear to have occurred through the fault of the Office, and the patentee respectfully requests correction thereof.

In equation 2, at column 8, line 15, " $\frac{s}{L} = \frac{M1}{Ml}$ " should be -- $\frac{s}{L} = \frac{M1}{M2}$ --;

In equation 3, at column 8, line 17, " $\frac{1}{f} = \frac{1}{M1} + \frac{1}{Ml}$ " should be -- $\frac{1}{f} = \frac{1}{M1} + \frac{1}{M2}$ --;

At column 8, line 4, "/is the focal length" should be --f is the focal length--;

At column 8, lines 7 and 8, "M1 is the distance between the first cylindrical lens 104 and the semiconductor substrate 106" should be -- M2 is the distance between the first cylindrical lens 104 and the semiconductor substrate 106--;

At column 9, lines 10-11, " $D_F = K_T / PC_p$, wherein K_T represents thermal conductivity, p represents density" should be -- $D_F = K_T / pC_p$, wherein K_T represents thermal conductivity, p represents density--;

At column 9, line 13, "density p of" should be --density p of--;

At column 9, line 39, "suicide" should be --silicide--;

At column 10, lines 10-11, "suicide" should be --silicide--;

At column 10, lines 19-21, "suicide layers 311b and 317b can be formed of a material such as molybdenum suicide (MoSix), tungsten suicide (WSix), tantalum silicide (TaSix), or titanium suicide (TiSix)" should be --silicide layers 311b and 317b can be formed of a material such as molybdenum silicide (MoSix), tungsten silicide (WSix), tantalum silicide (TaSix), or titanium silicide (TiSix)--;

At column 19, line 14, "suicide" should be --silicide--;

At column 19, line 16, "suicide" should be --silicide--.

The corrections are directed to mistakes in the patent incurred through the fault of the Office, possibly resulting from the Office's document scanning processes. As the errors were incurred through the fault of the Office, a fee is not believed to be necessary. Should it be determined that a fee is necessary, any deficiencies or overages in any fees due in connection with this patent and the requested actions should be applied to Deposit Account No. 50-2280.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285
Robinson Intellectual Property Law Office, P.C.
3975 Fair Ridge Drive
Suite 20 North
Fairfax, Virginia 22033
(571) 434-6789

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO : 7,737,053
DATED : June 15, 2010
INVENTOR(S) : Koichiro TANAKA et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

At column 8, line 15, please change " $\frac{s}{L} = \frac{M1}{Ml}$ " to -- $\frac{s}{L} = \frac{M1}{M2}$ --;

At column 8, line 17, please change " $\frac{1}{f} = \frac{1}{M1} + \frac{1}{Ml}$ " to -- $\frac{1}{f} = \frac{1}{M1} + \frac{1}{M2}$ --;

At column 8, line 4, please change "/is the focal length" to --f is the focal length--;

At column 8, lines 7 and 8, please change "M1 is the distance between the first cylindrical lens 104 and the semiconductor substrate 106" to -- M2 is the distance between the first cylindrical lens 104 and the semiconductor substrate 106--;

At column 9, lines 10-11, please change " $D_F = K_T / PC_p$, wherein K_T represents thermal conductivity, p represents density" to -- $D_F = K_T / \rho C_p$, wherein K_T represents thermal conductivity, ρ represents density--;

At column 9, line 13, please change "density p of" to --density ρ of--;

At column 9, line 39, please change "suicide" to --silicide--;

At column 10, lines 10-11, please change "suicide" to --silicide--;

At column 10, lines 19-21, please change "suicide layers 311b and 317b can be formed of a material such as molybdenum suicide (MoSix), tungsten suicide (WSix), tantalum silicide (TaSix), or titanium suicide (TiSix)" to --silicide layers 311b and 317b can be formed of a material such as molybdenum silicide (MoSix), tungsten silicide (WSix), tantalum silicide (TaSix), or titanium silicide (TiSix)--;

At column 19, line 14, please change "suicide" to --silicide--;

At column 19, line 16, please change "suicide" to --silicide--.

MAILING ADDRESS OF SENDER:

Eric J. Robinson
Robinson Intellectual Property Law Office
3975 Fair Ridge Drive, Suite 20 North
Fairfax, Virginia 22033

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